



ECH8653 — N-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- 4V drive.
- Best suited for LiB charging and discharging switch.
- Common-drain type.
- Halogen free compliance.

Specifications

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		20	V
Gate-to-Source Voltage	V_{GSS}		± 10	V
Drain Current (DC)	I_D		7.5	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	40	A
Allowable Power Dissipation	P_D	Mounted on a ceramic board (900mm 2 ×0.8mm) 1unit	1.4	W
Total Dissipation	P_T	Mounted on a ceramic board (900mm 2 ×0.8mm)	1.5	W
Channel Temperature	T_{ch}		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1\text{mA}$, $V_{GS}=0\text{V}$	20			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20\text{V}$, $V_{GS}=0\text{V}$			1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 8\text{V}$, $V_{DS}=0\text{V}$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10\text{V}$, $I_D=1\text{mA}$	1.0		2.4	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10\text{V}$, $I_D=4\text{A}$	3.4	5.8		S

Marking : WY

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ECH8653

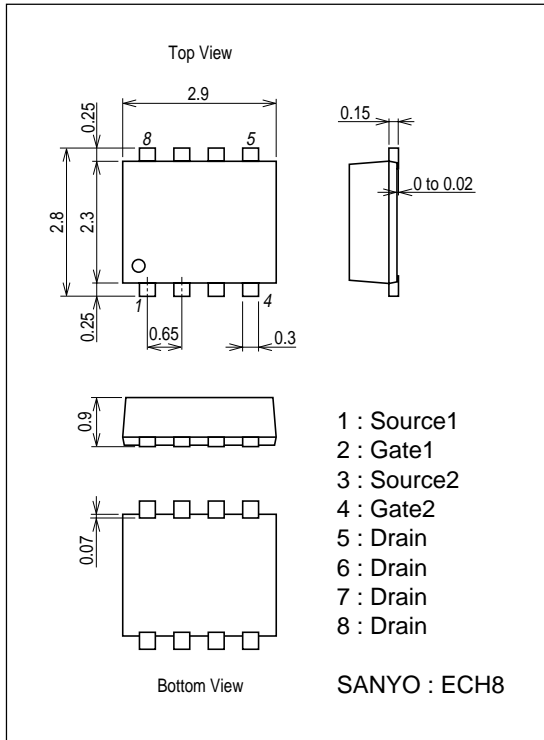
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=4A, V_{GS}=8V$	9	14	20	m Ω
	$R_{DS(on)2}$	$I_D=4A, V_{GS}=4V$	11	18	25	m Ω
Input Capacitance	C_{iss}	$V_{DS}=10V, f=1MHz$		1280		pF
Output Capacitance	C_{oss}	$V_{DS}=10V, f=1MHz$		170		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=10V, f=1MHz$		105		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit.		13		ns
Rise Time	t_r	See specified Test Circuit.		48		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit.		94		ns
Fall Time	t_f	See specified Test Circuit.		36		ns
Total Gate Charge	Q_g	$V_{DS}=10V, V_{GS}=8V, I_D=7.5A$		18.5		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=10V, V_{GS}=8V, I_D=7.5A$		2.7		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=10V, V_{GS}=8V, I_D=7.5A$		3.1		nC
Diode Forward Voltage	V_{SD}	$I_S=7.5A, V_{GS}=0V$		0.82	1.2	V

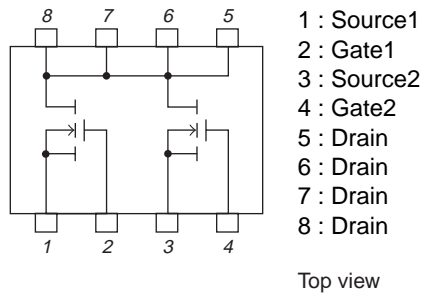
Package Dimensions

unit : mm (typ)

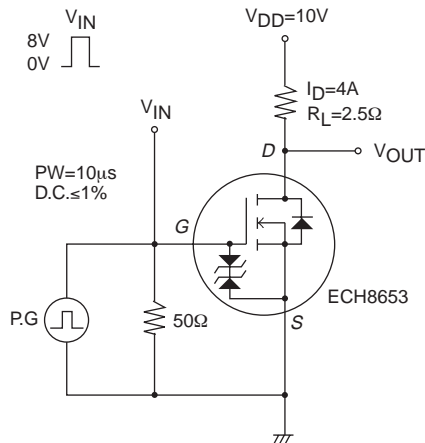
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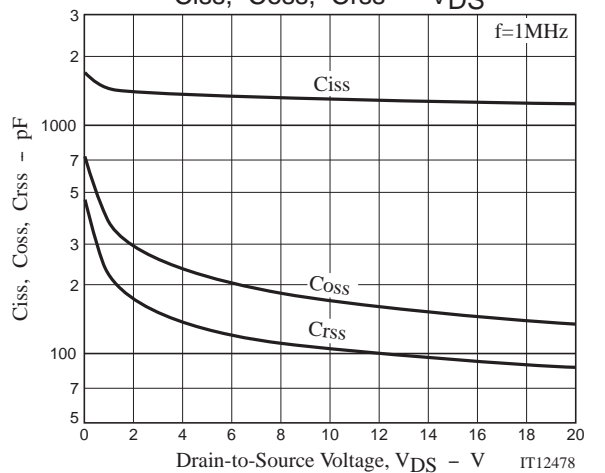
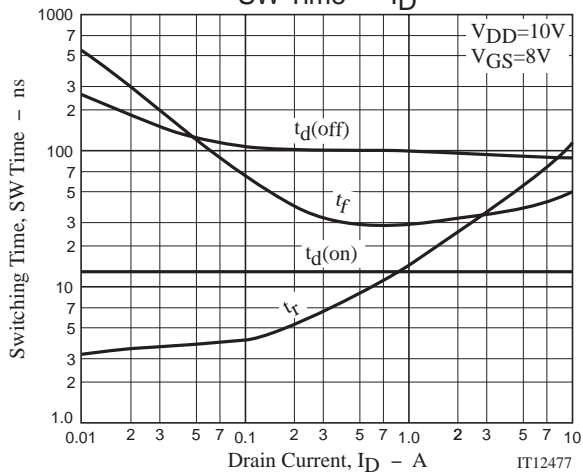
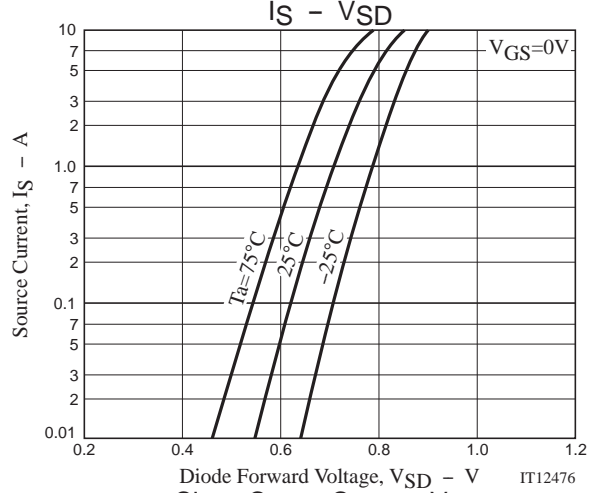
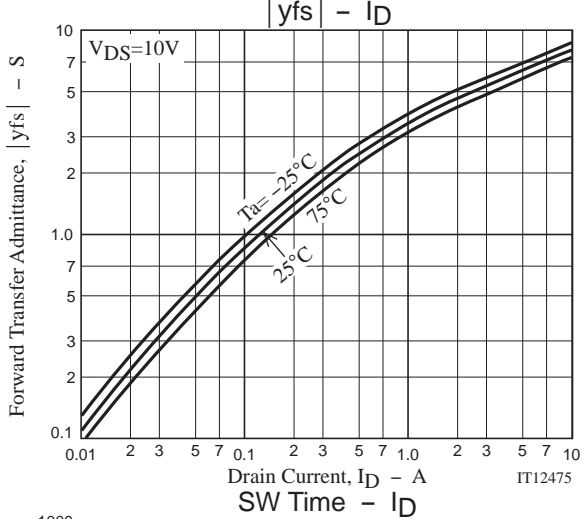
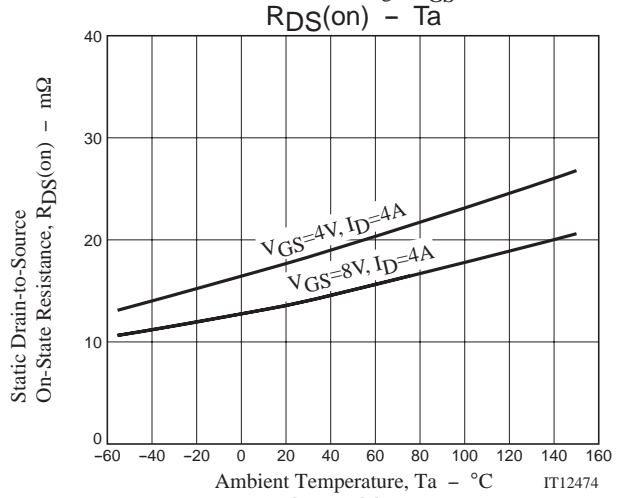
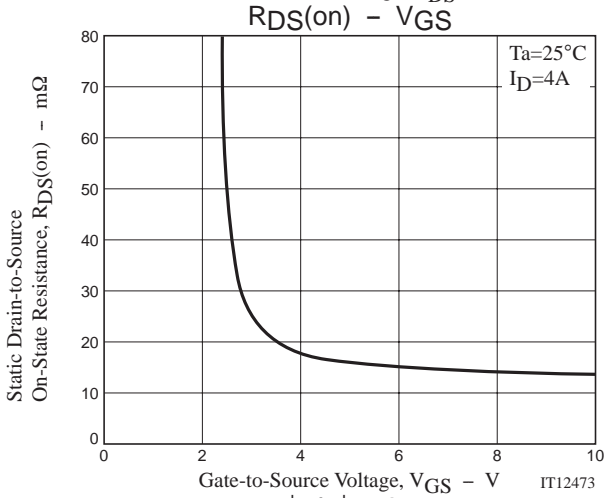
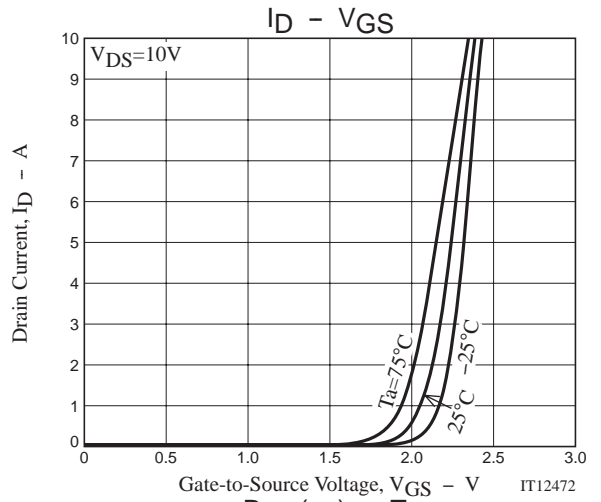
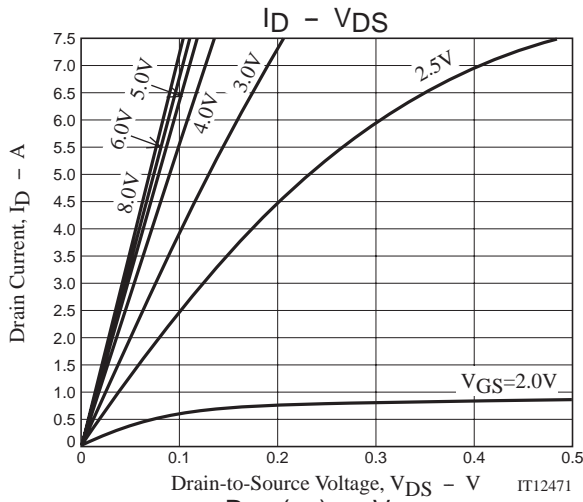


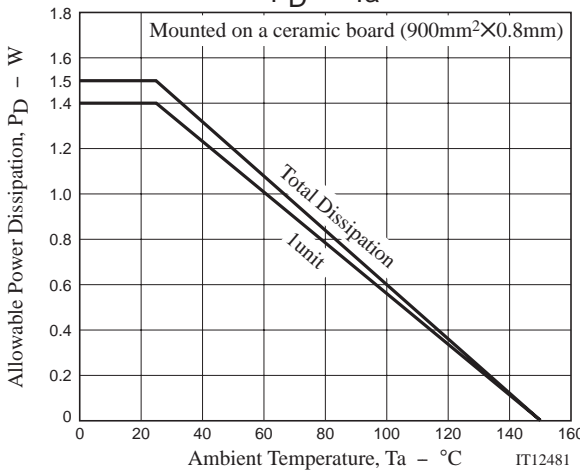
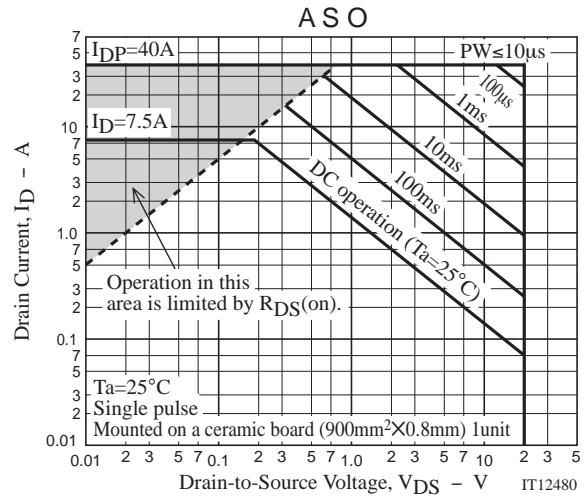
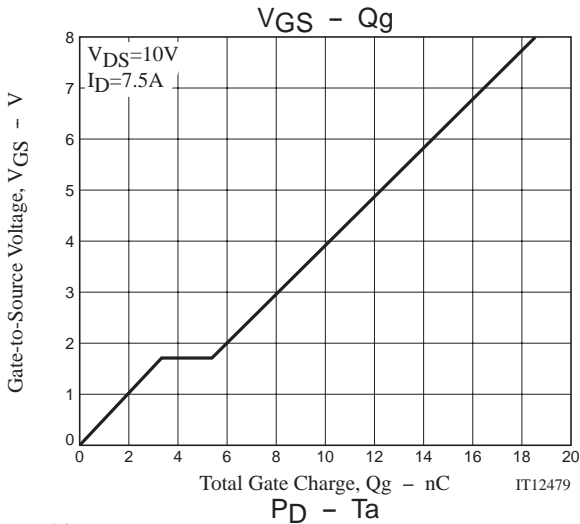
Electrical Connection



Switching Time Test Circuit







Note on usage : Since the ECH8653 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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